DATASHEET

1.6mm Round Subminiature Reverse Package Phototransistor

PT26-21C/TR8

Features

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Pb free
- The product itself will remain within RoHS compliant version.
- Compliance with EU REACH

Descriptions

- PT26-21C/TR8 is a phototransistor in miniature SMD package which is molded in a water clear with spherical top view lens. The device is Spectrally matched to visible and infrared emitting diode.

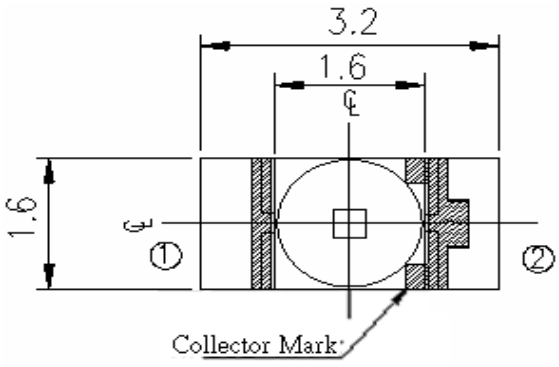
Applications

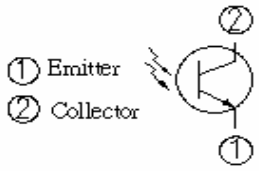
- Miniature switch
- Counters and sorter
- Position sensor
- Infrared applied system
- Encoder

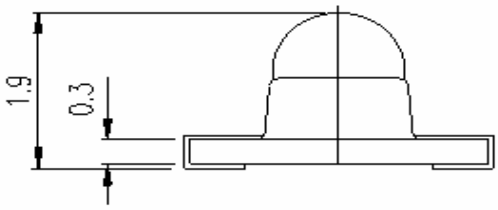
Device Selection Guide

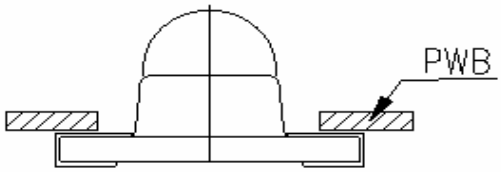
Part Category	Chip Material	Lens Color
PT	Silicon	Water Clear

Package Dimensions

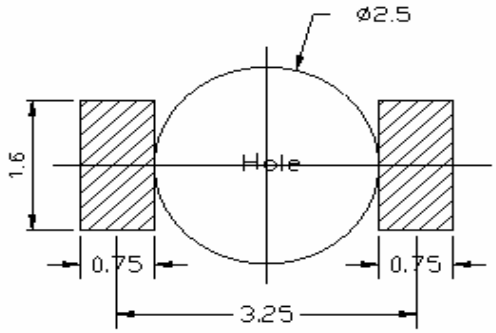


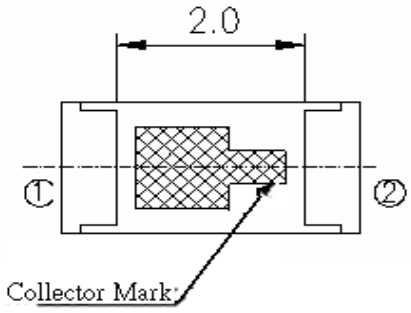






For Reflow Soldering (Propose)





Notes: 1.All dimensions are in millimeters
2.Tolerances unless dimensions ±0.1mm
3.Suggested pad dimension is just for reference only
Please modify the pad dimension based on individual need

Absolute Maximum Ratings (Ta=25℃)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85	℃
Storage Temperature	T_{stg}	-40 ~ +85	℃
Soldering Temperature *1	T_{sol}	260	℃
Power Dissipation at(or below) 25℃Free Air Temperature	P_d	75	mW

Notes: *1:Soldering time≦5 seconds.

Electro-Optical Characteristics (Ta=25℃)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Rang Of Spectral Bandwidth	$\lambda_{0.5}$	---	400	---	1100	nm
Wavelength Of Peak Sensitivity	λ_P	---	---	940	---	nm
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=100μA Ee=0mW/cm^2	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	I_E=100μA Ee=0mW/cm^2	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2mA Ee=1mW/cm^2	---	---	0.4	V
Collector Dark Current	I_{CEO}	V_{CE}=20V Ee=0mW/cm^2	---	---	100	nA
On State Collector Current	$I_{C(ON)}$	V_{CE}=5V Ee=1mW/cm^2	0.3	2.6	---	mA

Typical Electro-Optical Characteristics Curves

Fig.1 Spectral Sensitivity

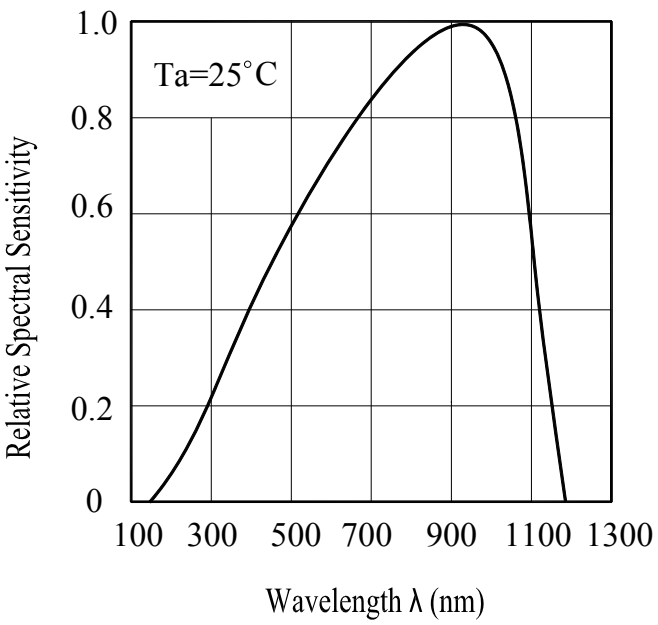


Fig.2 Collector Current vs. Irradiance

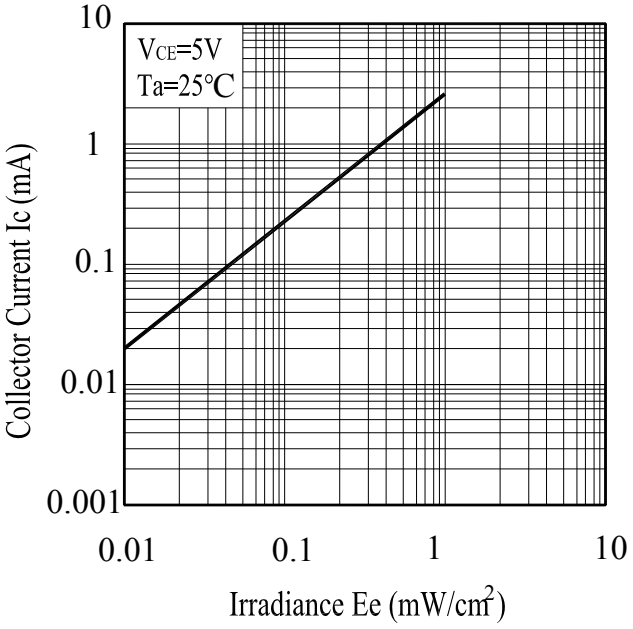
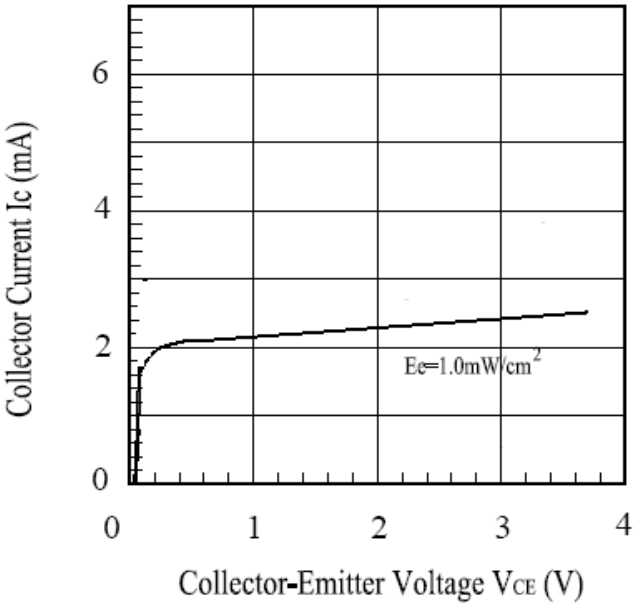


Fig.3 Collector Current vs. Collector-EmitterVoltage



Precautions For Use

1. Over-current-proof

   Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (Burn out will happen).

2. Storage

   2.1 Do not open moisture proof bag before the products are ready to use.

   2.2 Before opening the package, the Phototransistor should be kept at 10℃~30℃ and 90%RH or less.

   2.3 The Phototransistor suggested be used within one year.

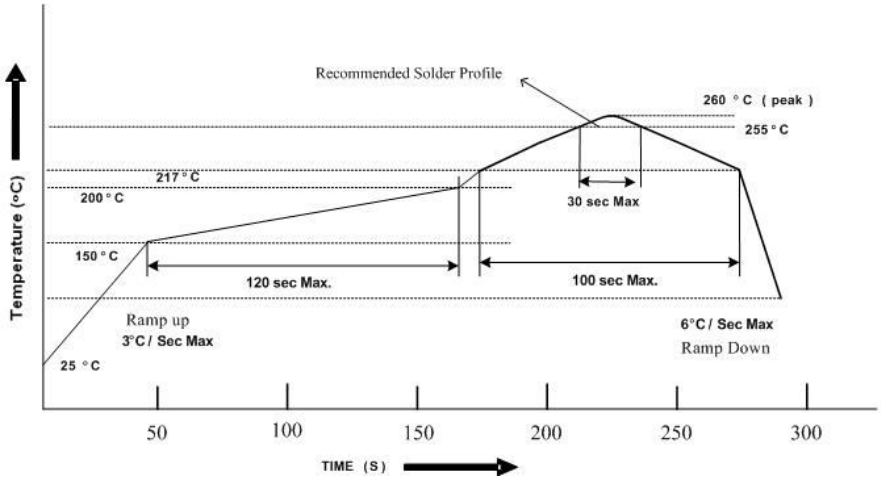
   2.4 After opening the package, the devices must be stored at 10°C~30°C and ≤ 60%RH, and used within 168 hours (floor life). If unused Phototransistor remain, it should be stored in moisture proof packages.

   2.5 If the moisture absorbent material (desiccant material) has faded or unopened bag has exceeded the shelf life or devices (out of bag) have exceeded the floor life, baking treatment is required.

   2.6 If baking is required, refer to IPC/JEDEC J-STD-033 for bake procedure or recommend the following conditions:
   96 hours at 60°C ± 5°C and < 5 % RH (reeled/tubed/loose units)

3. Soldering Condition

   3.1 Lead solder temperature profile



   3.2 Reflow soldering should not be done more than two times.

   3.3 When soldering, do not put stress on the Phototransistor during heating.

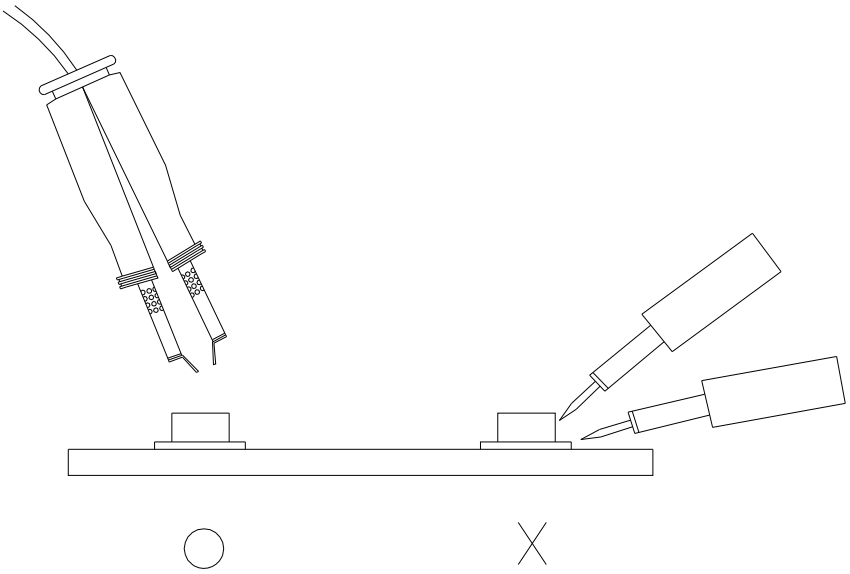
   3.4 After soldering, do not warp the circuit board.

4.Soldering Iron

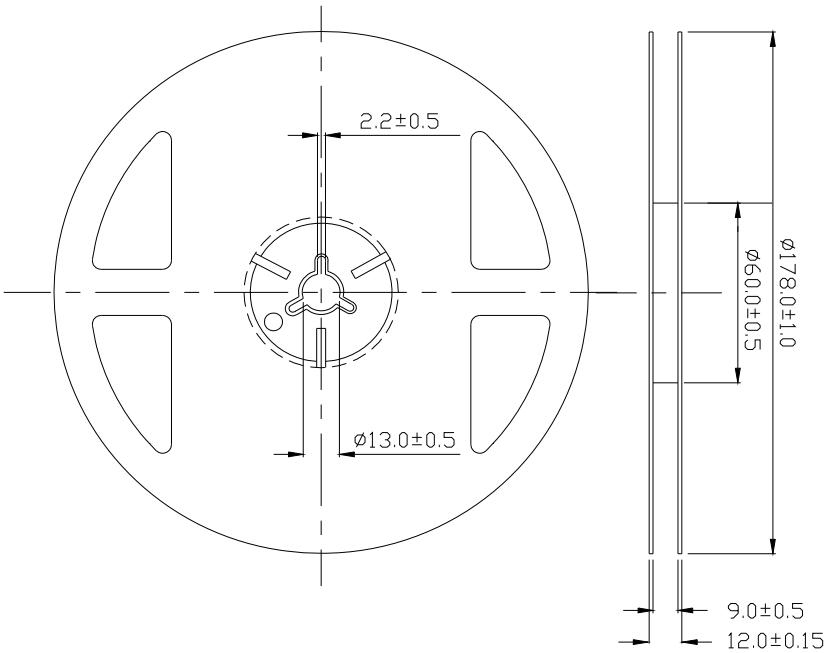
Each terminal is to go to the tip of soldering iron temperature less than 350℃ for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

5.Repairing

Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.

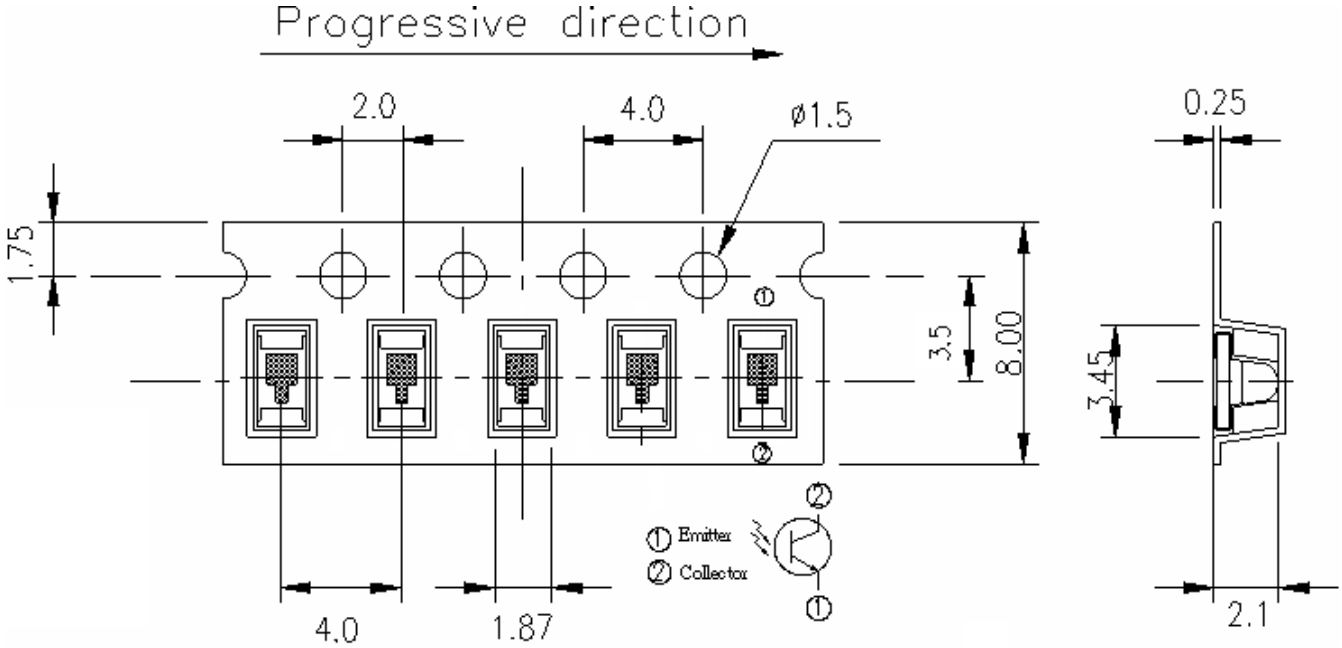


Package Dimensions



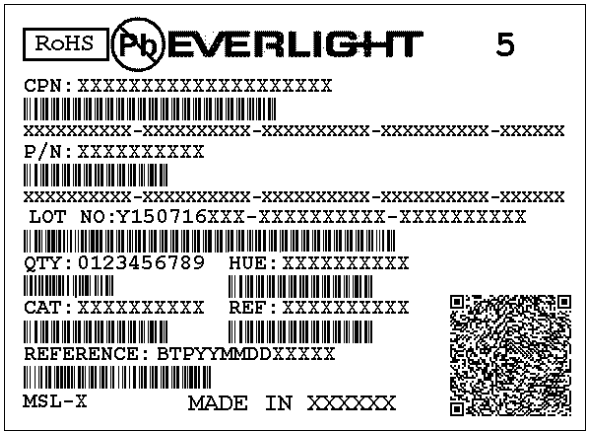
Note: The tolerances unless mentioned are ±0.1mm, Unit: mm

Carrier Tape Dimensions: (Loaded Quantity: 1500pcs/reel)



Note: The tolerances unless mentioned are ±0.1, unit=mm.

Label Form Specification



CPN: Customer's Production Number
P/N : Production Number
LOT No: Lot Number
QTY: Packing Quantity
HUE: Peak Wavelength
CAT: Ranks
REF: Reference
MSL-X: MSL Level
Made In: Manufacture place

Notes

1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
2. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
3. When using this product, please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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EVERLIGHT ELECTRONICS CO., LTD.
Office: No. 6-8, Zhonghua Rd., Shulin Dist.,
New Taipei City 23860, Taiwan
Tel: 886-2-2685-6688
Fax: 886-2685-2699，6897
http://www.everlight.com